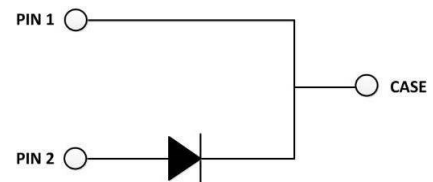


# 3<sup>rd</sup> Generation 1200V/20A SiC Schottky Barrier Diode

## Features

- AEC-Q101 qualified
- Revolutionary semiconductor material - Silicon Carbide (SiC)
- No reverse recovery
- High-speed switching performance
- Temperature-independent switching behavior
- System cost / size savings due to reduced cooling requirements
- Junction temperature range from -55°C to 175°C
- RoHS compliant



Package Type: TO-220-2L

## Potential Applications

- DC/DC converter for EV/HEV
- On board charger (OBC)



## Description

The ADS120J020C3 SiC Schottky Barrier Diode (SBD) has been developed using Sanan’s advanced 3<sup>rd</sup> generation SiC SBD technology with the highest performance and reliability. It registers higher efficiency, higher operation temperature and lower loss and can be operated at higher frequency than Si-based solutions. As to the Schottky structure, it shows no recovery at turn-off and allows a low leakage current with reverse voltage up to 1200V. It can contribute to system miniaturization and achieve lightweight system design. Using RoHS compliant components and being AEC-Q101 qualified, it is qualified for use in automotive application.

## Product Specifications

Device	V <sub>RRM</sub>	I <sub>F</sub> (135°C)	V <sub>F</sub> (25°C)	Q <sub>c</sub>	Marking
ADS120J020C3	1200V	30A	1.35V	108nC	DS120020C3

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**Table 1. Maximum Ratings**

(T<sub>c</sub> = 25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit	Test conditions
Repetitive peak reverse voltage	V <sub>RRM</sub>	1200	V	T <sub>C</sub> = 25°C
Surge peak reverse voltage	V <sub>RSM</sub>	1200		T <sub>C</sub> = 25°C
DC reverse voltage	V <sub>DC</sub>	1200		T <sub>C</sub> = 25°C
Continuous forward current	I <sub>F</sub>	64	A	T <sub>C</sub> = 25°C
		30		T <sub>C</sub> = 135°C
		20		T <sub>C</sub> = 155°C
Surge non-repetitive forward current	I <sub>FSM</sub>	180	A	T <sub>C</sub> = 25°C, t <sub>p</sub> = 10ms, half sine pulse
Surge repetitive forward current	I <sub>FRM</sub>	120	A	T <sub>C</sub> = 25°C, t <sub>p</sub> = 10ms, half sine wave D = 0.1
Power dissipation	P <sub>tot</sub>	283	W	T <sub>C</sub> = 25°C
i <sup>2</sup> t value	∫i <sup>2</sup> dt	162	A <sup>2</sup> s	T <sub>C</sub> = 25°C, t <sub>p</sub> = 10ms
Operating junction temperature	T <sub>j</sub>	-55~175	°C	
Storage temperature	T <sub>stg</sub>	-55~175	°C	
Mounting torque	M	1	Nm	M3 screw

**Table 2. Thermal Resistance**

Parameter	Symbol	Values			Unit	Test condition
		Min.	Typ.	Max.		
Thermal resistance from junction to case	R <sub>th(j-c)</sub>	/	0.53	/	°C/W	

**Table 3. Static Electrical Characteristics**

(T<sub>j</sub> = 25°C, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
DC blocking voltage	V <sub>DC</sub>	1200	/	/	V	I <sub>R</sub> = 100 μA
Forward voltage	V <sub>F</sub>	/	1.35	1.50	V	I <sub>F</sub> = 20A, T <sub>j</sub> = 25°C
		/	1.85	2.20		I <sub>F</sub> = 20A, T <sub>j</sub> = 175°C
Reverse current	I <sub>R</sub>	/	3	60	μA	V <sub>R</sub> = 1200V, T <sub>j</sub> = 25°C
		/	20	320		V <sub>R</sub> = 1200V, T <sub>j</sub> = 175°C

**Table 4. Dynamic Electrical Characteristics**

(T<sub>j</sub> = 25°C, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
Total capacitance	C	/	1565	/	pF	V <sub>R</sub> = 0V, f = 1MHz
		/	101	/		V <sub>R</sub> = 400V, f = 1MHz
		/	75	/		V <sub>R</sub> = 800V, f = 1MHz
Total capacitive charge	Q <sub>C</sub>	/	108	/	nC	V <sub>R</sub> = 800V
Capacitance stored energy	E <sub>C</sub>	/	31	/	μJ	V <sub>R</sub> = 800V

### Electrical Characteristic Diagrams

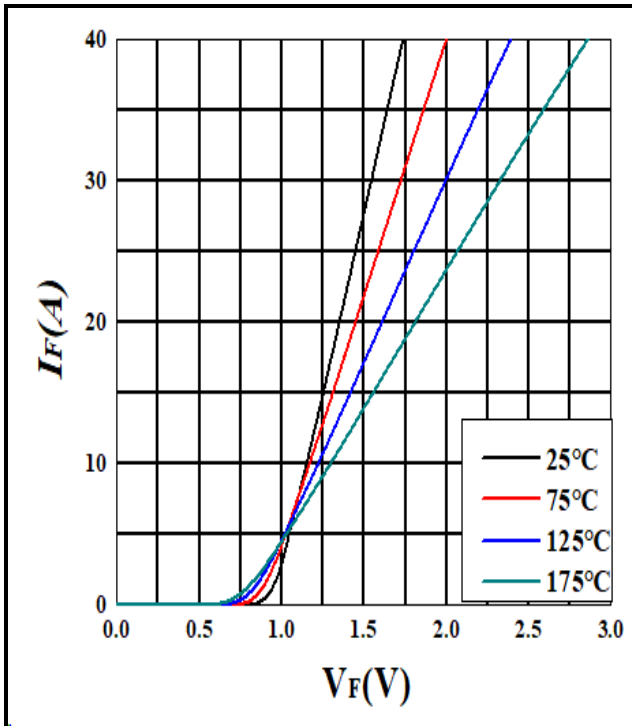


Figure 1. Forward characteristics

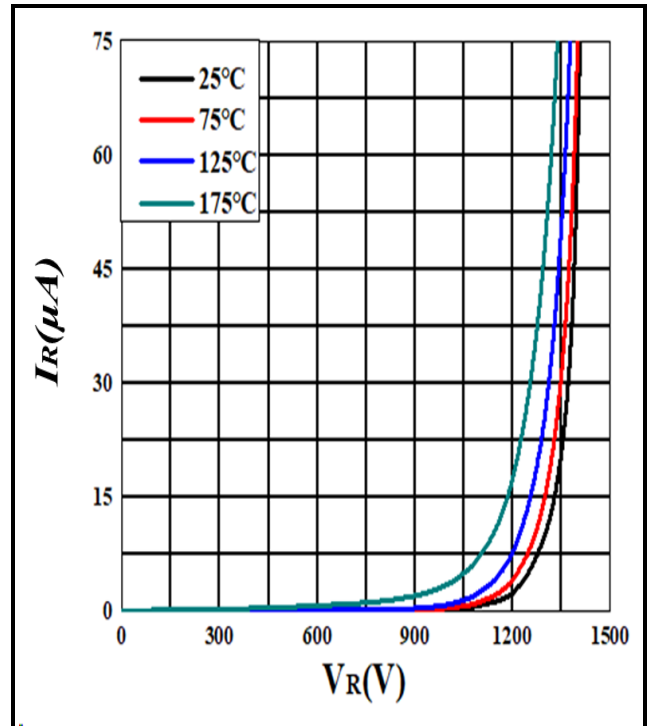


Figure 2. Reverse characteristics

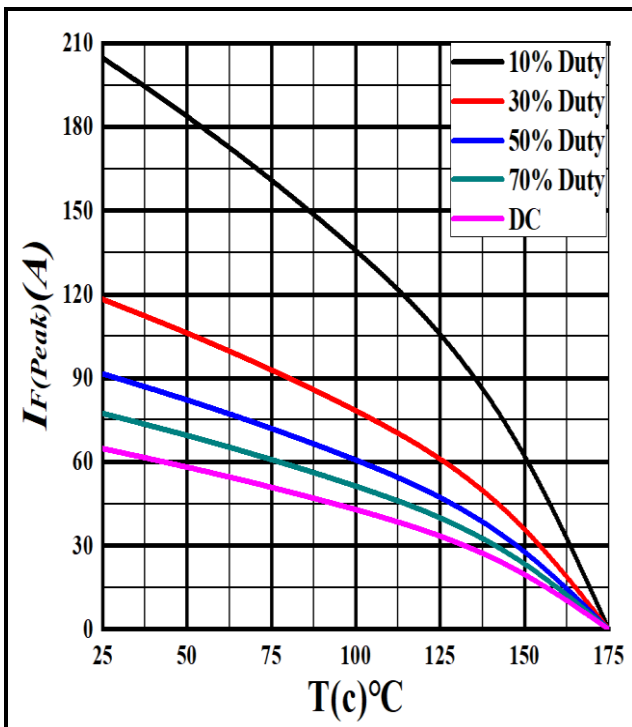


Figure 3. Current derating

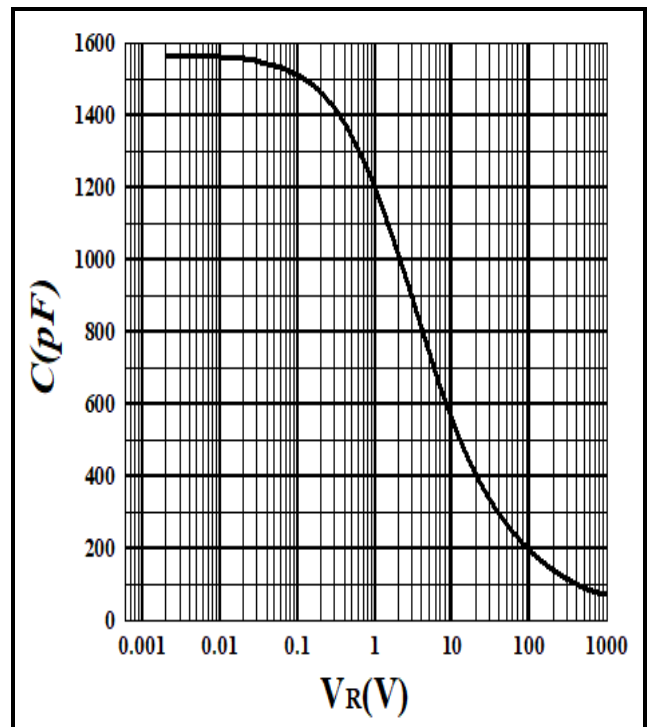


Figure 4. Capacitance vs. reverse voltage

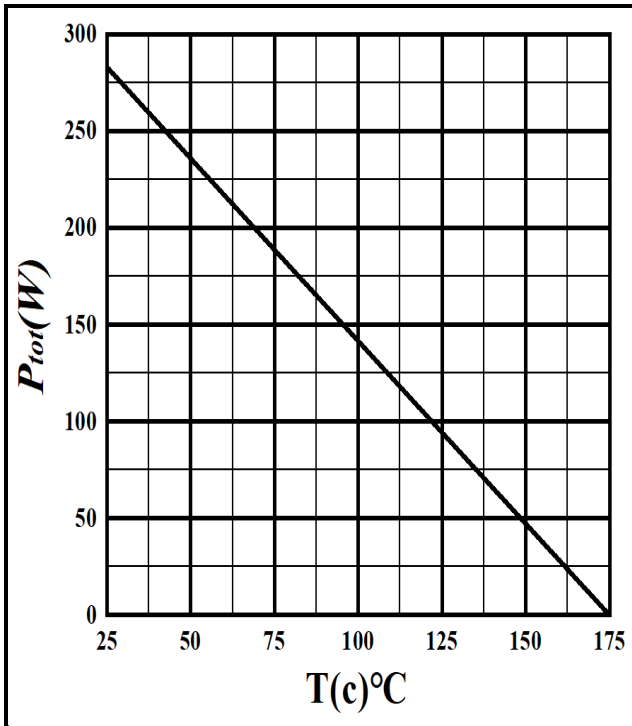


Figure 5. Power derating

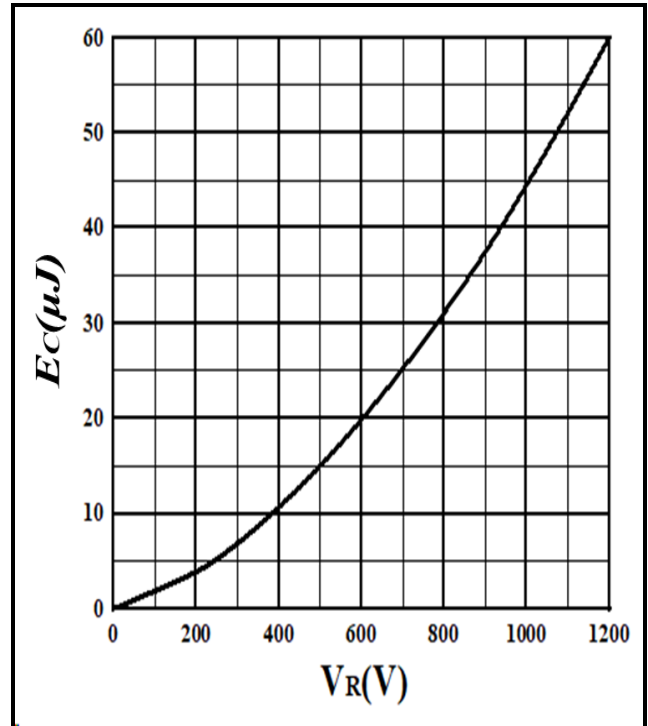


Figure 6. Capacitance stored energy

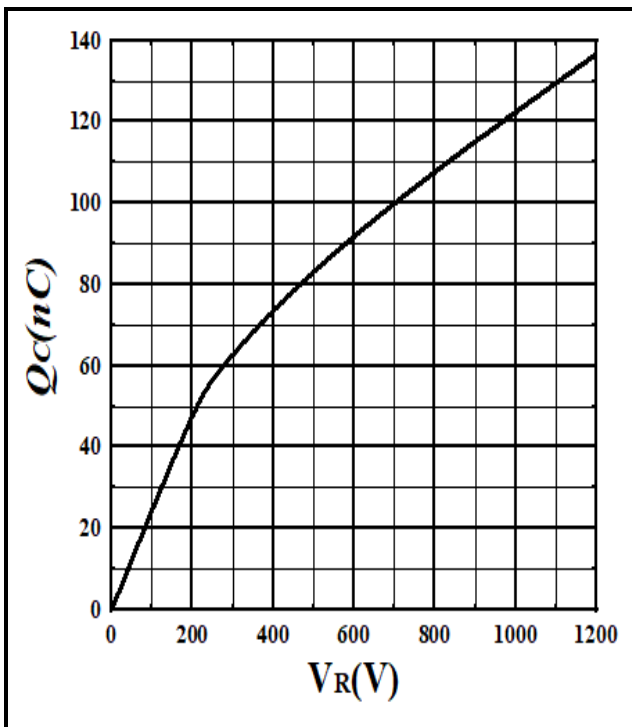
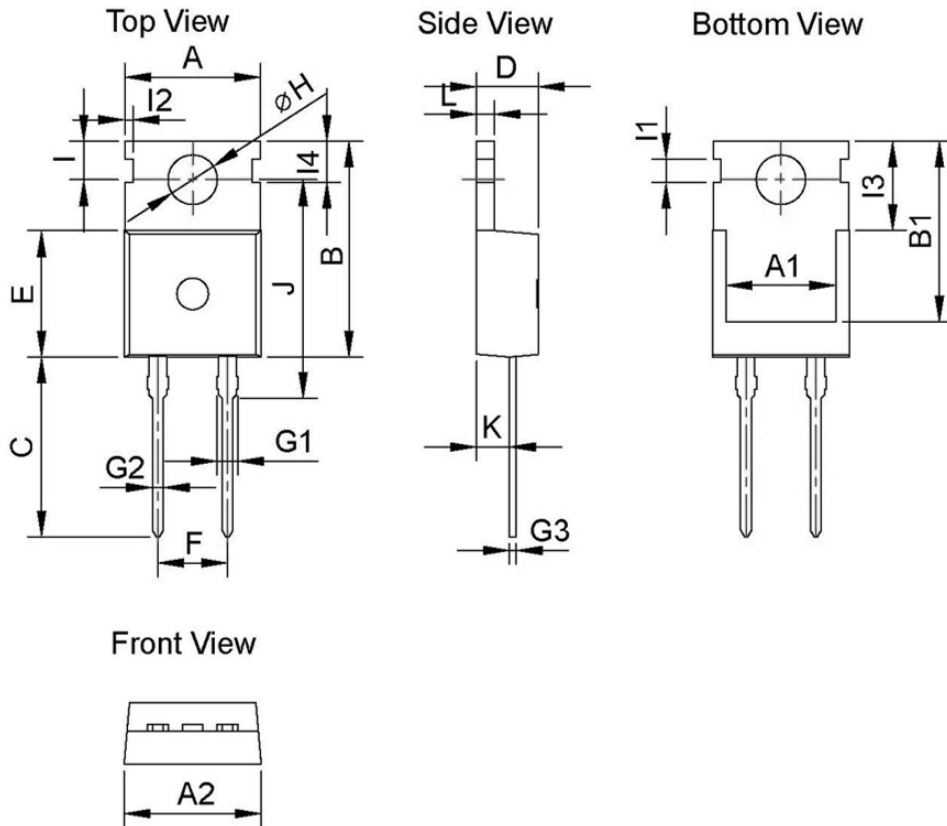


Figure 7. Total capacitance charge vs. reverse voltage

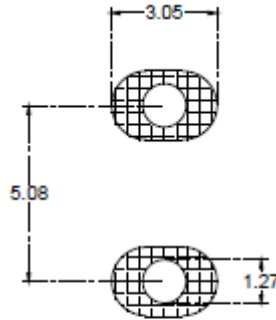
**Package Information**



Dimension unit: [mm]			
Symbol	Min	Nom	Max
A	9.66	9.90	10.28
A1	6.90	-	-
A2	9.80	10.00	10.20
B	15.60	15.70	15.80
B1	13.16 REF		
C	12.70	13.08	14.27
D	4.30	4.50	4.70
E	8.59	9.20	9.40
F	5.08 BSC		
G1	1.32	1.52	1.62
G2	0.70	0.80	0.95
G3	0.45	0.50	0.60
$\phi H$	3.53	3.60	3.70
I	2.70	2.80	2.90
I1	1.70 REF		
I2	0.59 REF		
I3	6.50 REF		
I4	3.00 REF		
J	15.70	15.90	16.25
K	2.20	2.40	2.60
L	1.15	1.30	1.40

## Recommended Solder Pad Layout

Note: All dimensions are in mm



TO-220-2L

## Ordering Information

Part number	ADS120J020C3-ASATH
Package	TO-220-2L
Unit quantity	1000 EA
Packing type	Tube



## Important Notices – Read Carefully

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